

Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	-0.029	—	V/ $^\circ\text{C}$	Reference to 25°C , $I_D = -1\text{mA}$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.60	Ω	$V_{GS} = -10V, I_D = -0.60A$ ③
		—	—	1.0		$V_{GS} = -4.5V, I_D = -0.30A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-1.0	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	0.44	—	—	S	$V_{DS} = -10V, I_D = -0.30A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -24V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -24V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -20V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 20V$
Q_g	Total Gate Charge	—	3.4	5.1	nC	$I_D = -0.60A$
Q_{gs}	Gate-to-Source Charge	—	0.52	0.78		$V_{DS} = -24V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	1.1	1.7		$V_{GS} = -10V$, See Fig. 6 and 9 ③
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	$V_{DD} = -15V$
t_r	Rise Time	—	8.2	—		$I_D = -0.60A$
$t_{d(off)}$	Turn-Off Delay Time	—	23	—		$R_G = 6.2\Omega$
t_f	Fall Time	—	16	—		$R_D = 25\Omega$, See Fig. 10 ③
C_{iss}	Input Capacitance	—	75	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	37	—		$V_{DS} = -25V$
C_{rss}	Reverse Transfer Capacitance	—	18	—		$f = 1.0\text{MHz}$, See Fig. 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-0.54	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-4.8		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	$T_J = 25^\circ\text{C}, I_S = -0.60A, V_{GS} = 0V$ ③
t_{rr}	Reverse Recovery Time	—	26	39	ns	$T_J = 25^\circ\text{C}, I_F = -0.60A$
Q_{rr}	Reverse Recovery Charge	—	20	30	nC	$di/dt = 100A/\mu s$ ③

Notes:

① Repetitive rating; pulse width limited by
max. junction temperature. (See fig. 11)③ Pulse width $\leq 300\mu s$; duty cycle $\leq 2\%$.② $I_{SD} \leq -0.60A, di/dt \leq 110A/\mu s, V_{DD} \leq V_{(BR)DSS},$
 $T_J \leq 150^\circ\text{C}$ ④ Surface mounted on FR-4 board, $t \leq 5\text{sec}$.

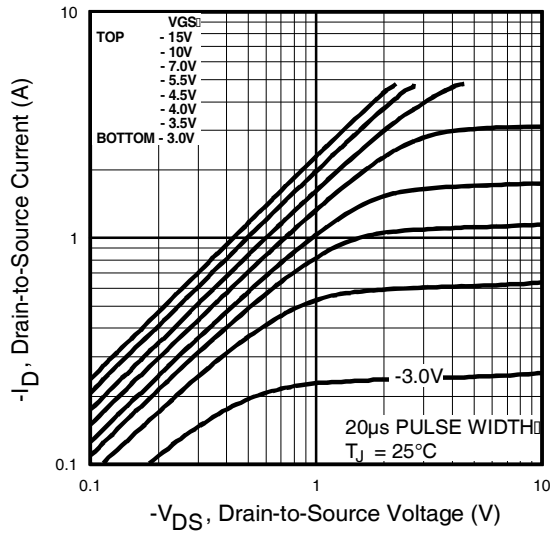


Fig 1. Typical Output Characteristics

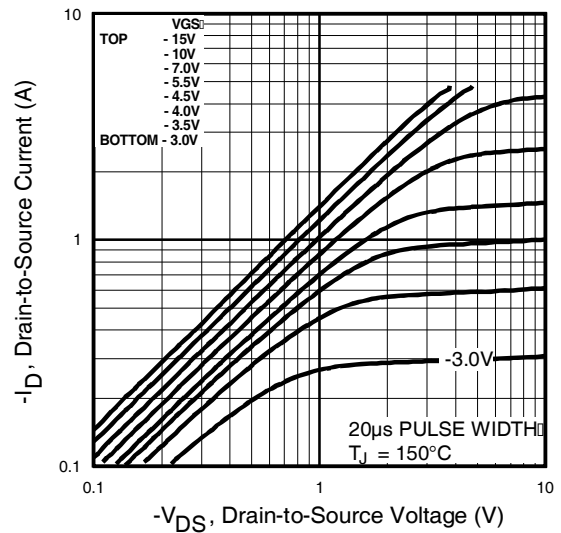


Fig 2. Typical Output Characteristics

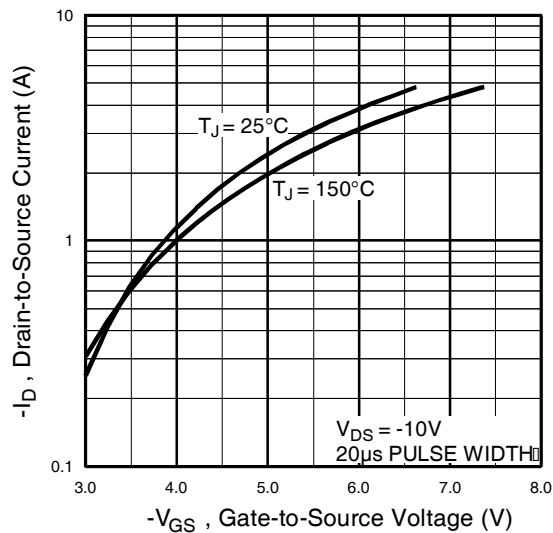


Fig 3. Typical Transfer Characteristics

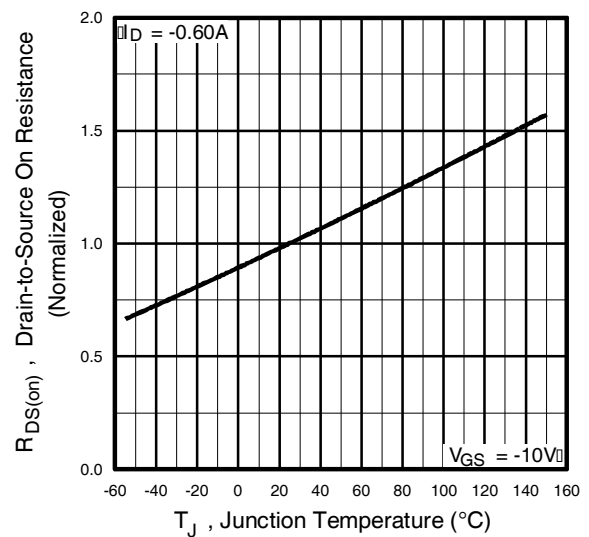


Fig 4. Normalized On-Resistance
Vs. Temperature

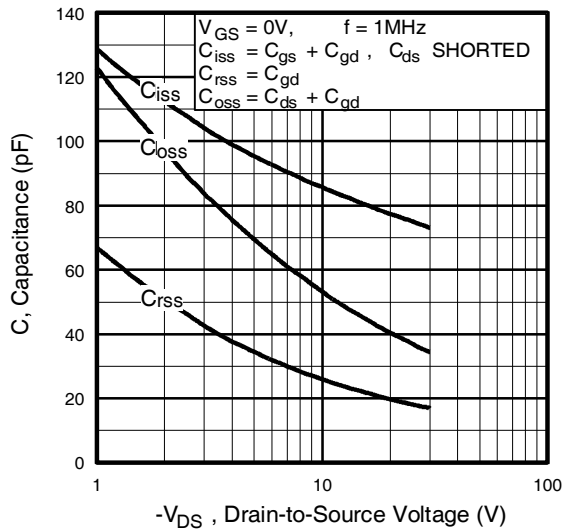


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

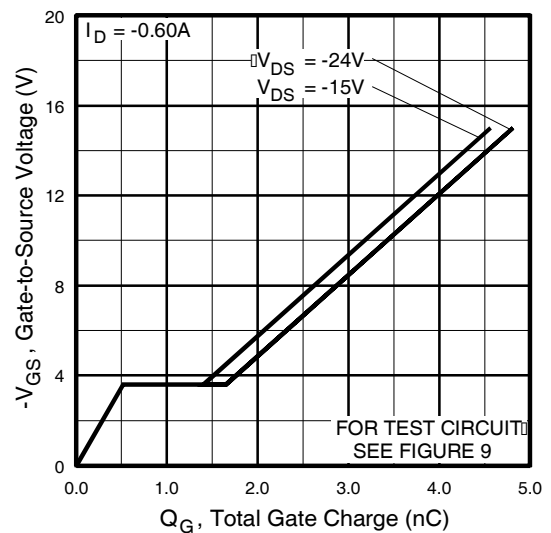


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

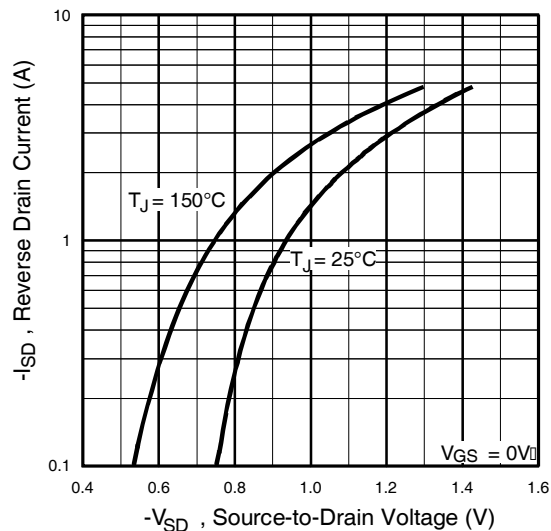


Fig 7. Typical Source-Drain Diode Forward Voltage

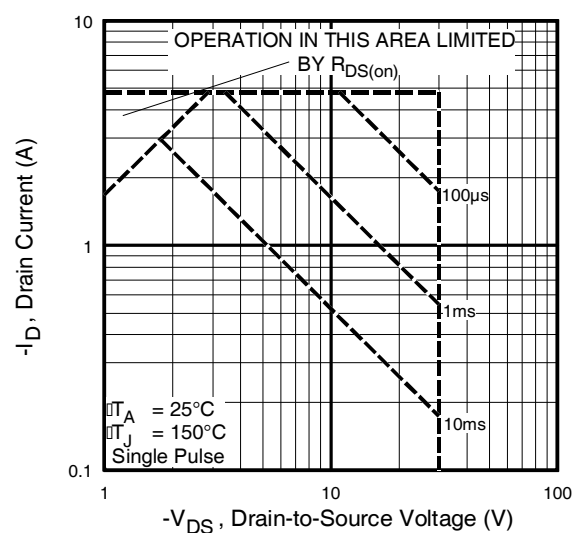


Fig 8. Maximum Safe Operating Area

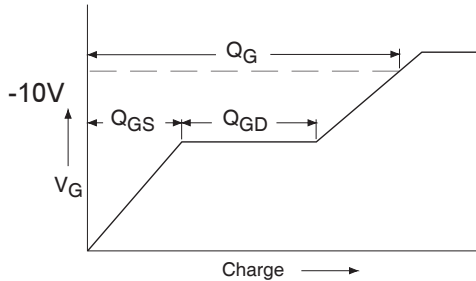


Fig 9a. Basic Gate Charge Waveform

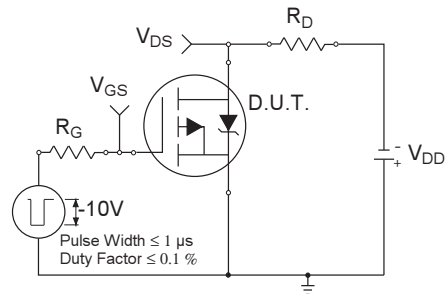


Fig 10a. Switching Time Test Circuit

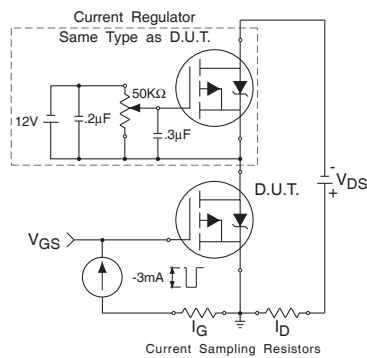


Fig 9b. Gate Charge Test Circuit

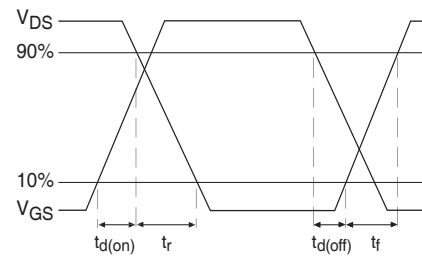


Fig 10b. Switching Time Waveforms

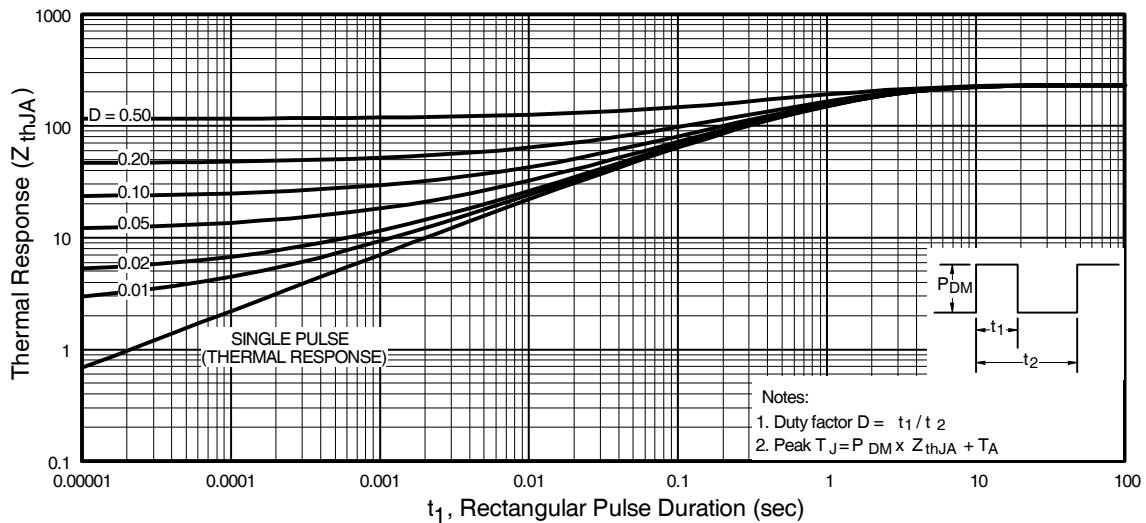
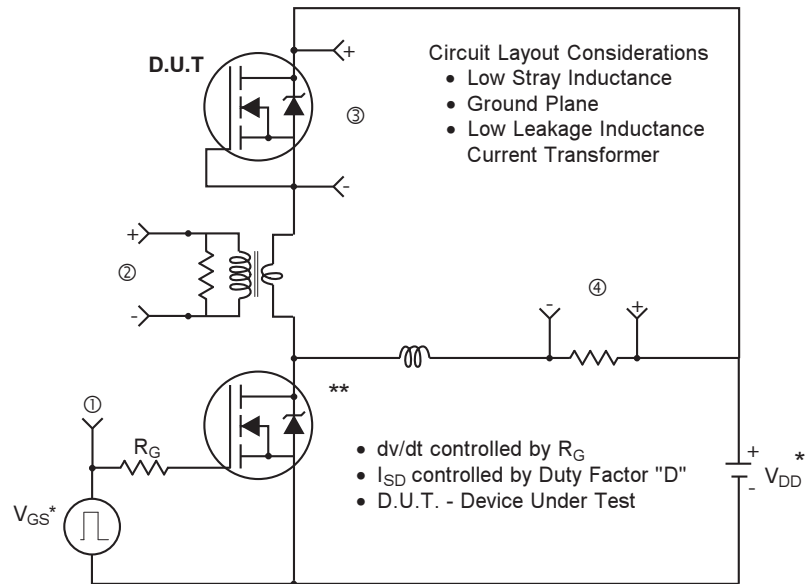


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements

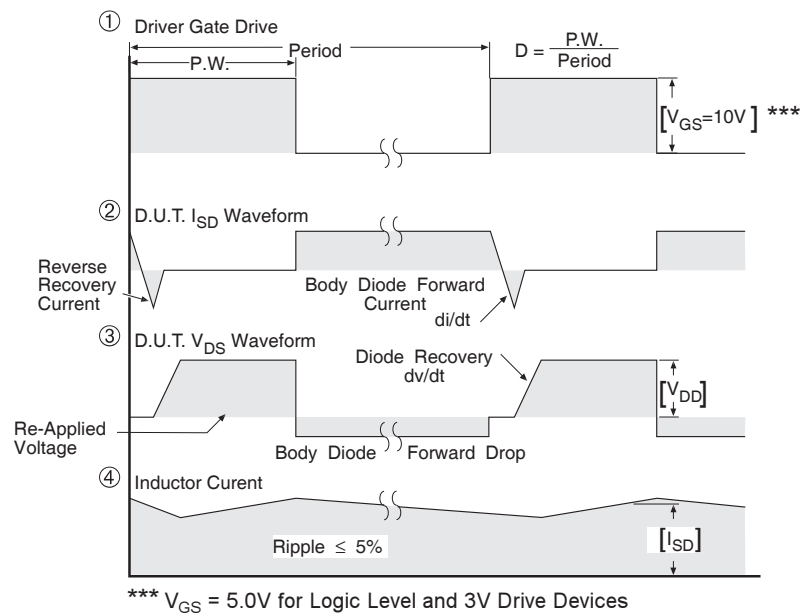
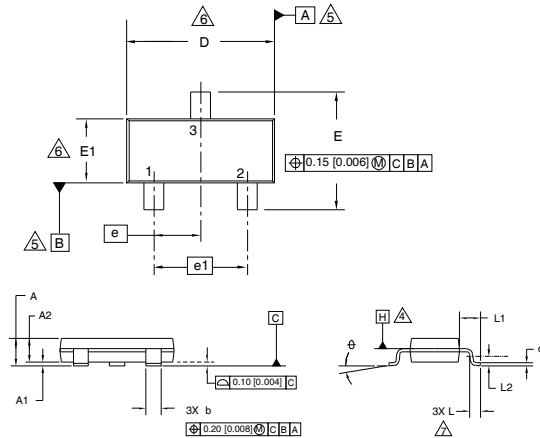


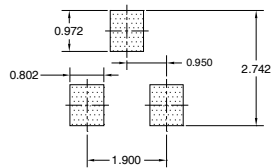
Fig 13. For P-Channel HEXFETS

Micro3 (SOT-23) (Lead-Free) Package Outline

Dimensions are shown in millimeters (inches)



Recommended Footprint



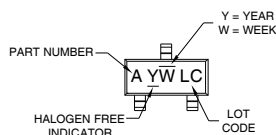
DIMENSIONS				
SYMBOL	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	0.89	1.12	0.035	0.044
A1	0.01	0.10	0.0004	0.004
A2	0.88	1.02	0.035	0.040
b	0.30	0.50	0.012	0.020
c	0.08	0.20	0.003	0.008
D	2.80	3.04	0.110	0.120
E	2.10	2.64	0.083	0.104
E1	1.20	1.40	0.047	0.055
e	0.95	BSC	0.037	BSC
e1	1.90	BSC	0.075	BSC
L	0.40	0.60	0.016	0.024
L1	0.54	REF	0.021	REF
L2	0.25	BSC	0.010	BSC
Ø	0	8	0	8

NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1994
2. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
3. CONTROLLING DIMENSION: MILLIMETER.
4. DATUM PLANE H IS LOCATED AT THE MOLD PARTING LINE.
5. DATUM A AND B TO BE DETERMINED AT DATUM PLANE H.
6. DIMENSIONS D AND E1 ARE MEASURED AT DATUM PLANE H. DIMENSIONS DOES NOT INCLUDE MOLD PROTRUSIONS OR INTERLEAD FLASH. MOLD PROTRUSIONS OR INTERLEAD FLASH SHALL NOT EXCEED 0.25 MM (0.010 INCH) PER SIDE.
7. DIMENSION L IS THE LEAD LENGTH FOR SOLDERING TO A SUBSTRATE.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-236 AB.

Micro3 (SOT-23 / TO-236AB) Part Marking Information

Micro3 / SOT-23 Package Marking



PART NUMBER CODE REFERENCE:

A = IRLML2402
B = IRLML2803
C = IRLML2402
D = IRLML5103
E = IRLML6402
F = IRLML6401
G = IRLML2502
H = IRLML5203

Note: A line above the work week
(as shown here) indicates Lead-free

W = (1-26) IF PRECEDED BY LAST DIGIT OF CALENDAR YEAR

YEAR	Y	WORK WEEK	W
2001	1	01	A
2002	2	02	B
2003	3	03	C
2004	4	04	D
2005	5		
2006	6		
2007	7		
2008	8		
2009	9		
2010	0	24	X
		25	Y
		26	Z

W = (27-52) IF PRECEDED BY A LETTER

YEAR	Y	WORK WEEK	W
2001	A	27	A
2002	B	28	B
2003	C	29	C
2004	D	30	D
2005	E		
2006	F		
2007	G		
2008	H		
2009	J		
2010	K	50	X
		51	Y
		52	Z

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package>

www.irf.com

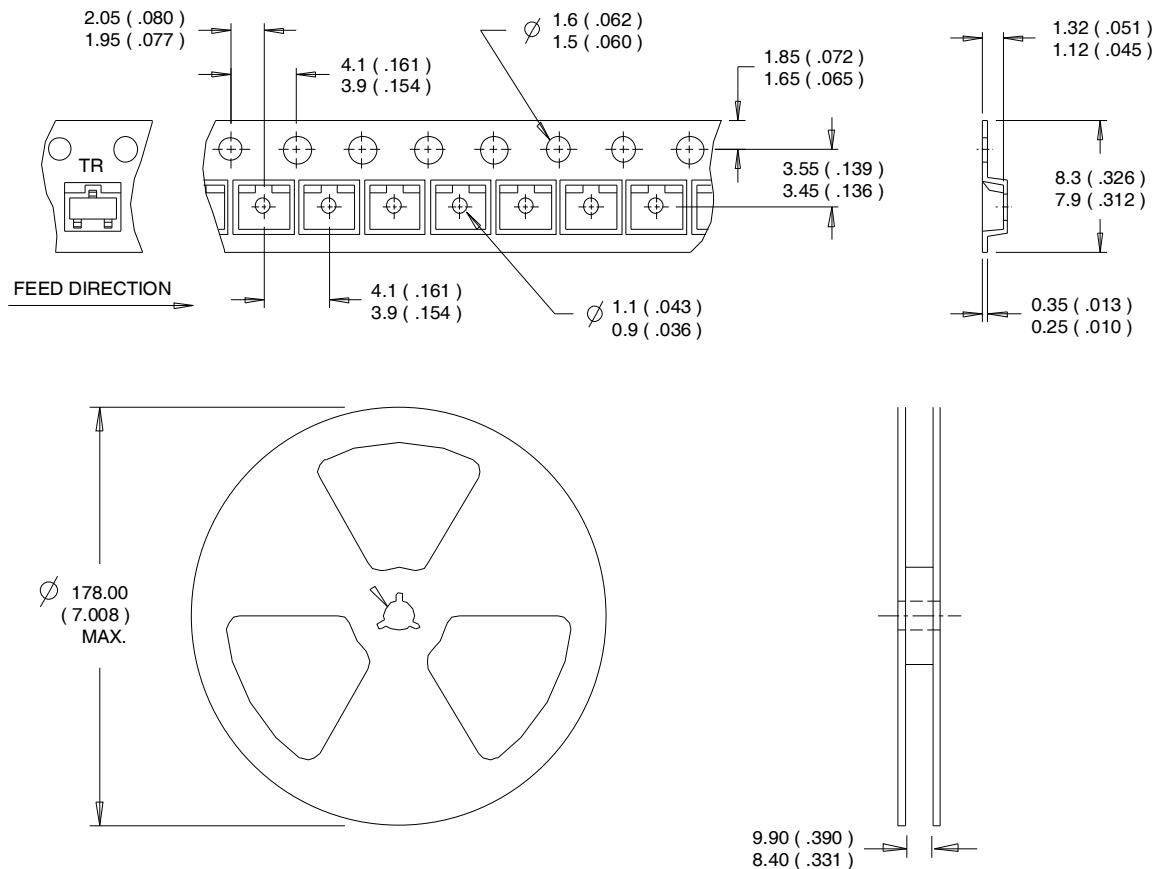
IRLML5103

International
IOR Rectifier

Tape & Reel Information

SOT-23

Dimensions are shown in millimeters (inches)



NOTES:

1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.

International
IOR Rectifier

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